

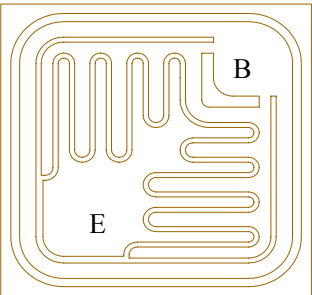
8550B Silicon PNP Epitaxial Transistor

Description :The 8550B is designed for use in 2W output amplifier of portable radios
in class B push-pull operation

Features: ●Excellent h_{FE} Linearity

●Complementary to 8050B

Chip Appearance

	Chip Size		580um × 580um
	Chip Thickness		210 ± 20um
	Bonding Pad Size	Base	115um × 115um
		Emitter	120um × 120um
	Front Metal		Al
	Backside Metal		Au
	Scribe line width		50um
	Wafer Size		6 inch (45594)

Electrical Characteristics($T_a=25^{\circ}\text{C}$)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=-35\text{V}, I_E=0$		-0.1	uA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$		-0.1	uA
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=-0.1\text{mA}$	-40		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=-1\text{mA}$	-25		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=-0.1\text{mA}$	-5.0		V
DC Current Gain	h_{FE}	$V_{CE}=-1\text{V}, I_C=-100\text{mA}$	100	400	
Collector Saturation Voltage	$V_{CE(sat)}$	$I_C=-800\text{mA}, I_B=-80\text{mA}$		-0.5	V

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